Product data sheet

1. General description

NPN low V_{CEsat} transistor in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS5420D

2. Features and benefits

- · Very low collector-emitter saturation resistance
- Ultra low collector-emitter saturation voltage
- · 4 A continuous collector current
- Up to 15 A peak current
- · High efficiency due to less heat generation

3. Applications

- · Power management functions
- Charging circuits
- · DC-to-DC conversion
- · MOSFET gate driving
- · Power switches (e.g. motors, fans)
- Thin Film Transistor (TFT) backlight inverter

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	20	٧
I _C	collector current		[1]	-	-	4	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	15	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 4 A; I_B = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C		-	50	70	mΩ

[1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	С	collector		
2	С	collector	<u> </u>	
3	В	base		В—
4	E	emitter]
5	С	collector	TSOP6 (SOT457)	sym014
6	С	collector		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS4420D	TSOP6	plastic, surface-mounted package (SC-74; TSOP6); 6 leads	SOT457

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4420D	D4

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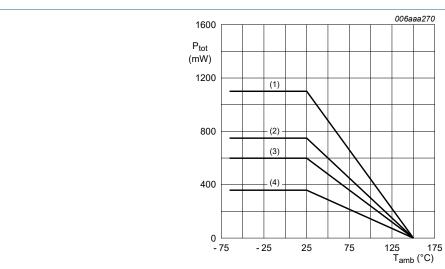
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	20	V
V _{CEO}	collector-emitter voltage	open base		-	20	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
Ic	collector current		[1]	-	4	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	15	Α
I _B	base current			-	0.8	Α
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	2	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	360	mW
			[3]	-	600	mW
			[4]	-	750	mW
			[1]	-	1.1	W
			[2] [5]	-	2.5	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [5] Operated under pulsed conditions: $\delta \le 10 \%$; $t_p \le 10 \text{ ms.}$



- (1) Ceramic PCB, Al_2O_3 , standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, mounting pad for collector 1 cm²
- (4) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	[2] [3] [4]	[1]	-	-	350	K/W
	junction to ambient		[2]	-	-	208	K/W
			[3]	-	-	160	K/W
			[4]	-	-	113	K/W
			[1] [5]	-	-	50	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	45	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Operated under pulsed conditions: $\delta \le 10^{\circ}$ %; $t_p \le 10^{\circ}$ ms.

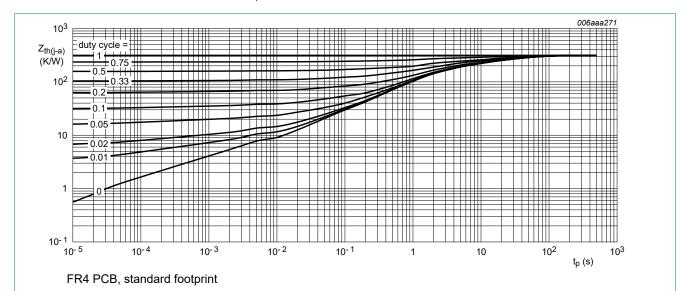
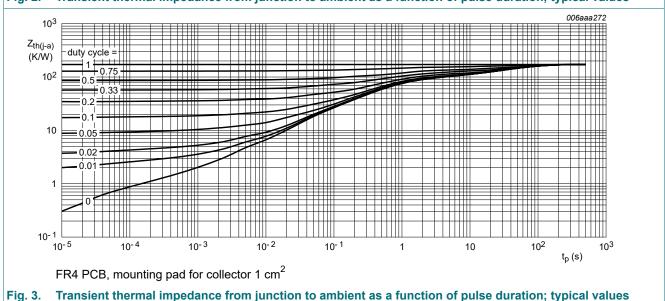


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

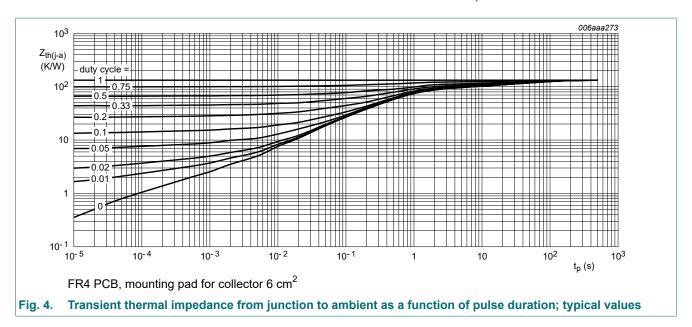


PBSS4420D

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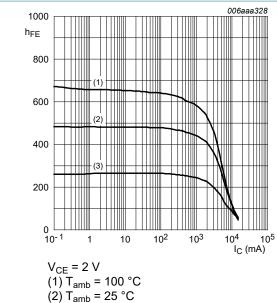
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10. Characteristics

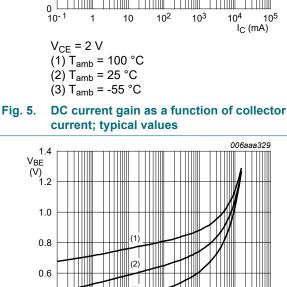
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{СВО}	collector-base cut-off	V _{CB} = 20 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 20 V; I _E = 0 A; T _j = 150 °C	-	-	50	μΑ
I _{CES}	collector-emitter cut-off current	V _{CE} = 20 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{ЕВО}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 0.5 A; T _{amb} = 25 °C	300	450	-	
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	300	430	-	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	250	400	-	
		V_{CE} = 2 V; I_{C} = 4 A; pulsed; $t_{p} \le 300 \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	200	310	-	
		V_{CE} = 2 V; I_{C} = 6 A; pulsed; $t_{p} \le 300 \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	100	230	-	
V _{CEsat}	collector-emitter	I _C = 0.5 A; I _B = 50 mA; T _{amb} = 25 °C	-	30	50	mV
	saturation voltage	I _C = 1 A; I _B = 50 mA; T _{amb} = 25 °C	-	60	90	mV
		I _C = 2 A; I _B = 200 mA; T _{amb} = 25 °C	-	110	150	mV
		I_C = 4 A; I_B = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	200	280	mV
		I_C = 6 A; I_B = 600 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	300	420	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 4 A; I_B = 400 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	50	70	mΩ
V_{BEsat}	base-emitter saturation	$I_C = 0.5 \text{ A}; I_B = 50 \text{ mA}; T_{amb} = 25 \text{ °C}$	-	0.79	0.85	V
	voltage	I_C = 1 A; I_B = 50 mA; T_{amb} = 25 °C	-	0.81	0.9	V
		I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.83	1	V
		I_C = 4 A; I_B = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	1	1.1	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 2 \text{ V}; I_{C} = 2 \text{ A}; T_{amb} = 25 \text{ °C}$	-	0.79	1	V
t _d	delay time	$V_{CC} = 12.5 \text{ V}; I_C = 3 \text{ A}; I_{Bon} = 0.15 \text{ A};$	-	12	-	ns
t _r	rise time	I _{Boff} = -0.15 A; T _{amb} = 25 °C	-	36	-	ns
ton	turn-on time		-	48	-	ns
t _s	storage time		-	230	-	ns
t _f	fall time		-	50	-	ns
t _{off}	turn-off time		-	280	-	ns
f _T	transition frequency	$V_{CE} = 10 \text{ V}; I_{C} = 0.1 \text{ A}; f = 100 \text{ MHz};$ $T_{amb} = 25 \text{ °C}$	-	100	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$	-	60	-	pF

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current; typical values



 $V_{CE} = 2 V$

0.4

0.2

10-1

(1) T_{amb} = -55 °C

(2) T_{amb} = 25 °C

(3) $T_{amb} = 100 \, ^{\circ}C$

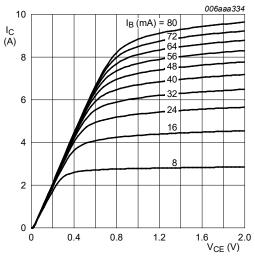
Fig. 7. Base-emitter voltage as a function of collector current; typical values

10²

10

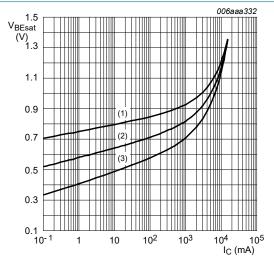
10³

10⁴ 10⁵ I_C (mA)



T_{amb} = 25 °C

Fig. 6. Collector current as a function of collectoremitter voltage; typical values



 $I_C/I_B = 20$

(1) T_{amb} = -55 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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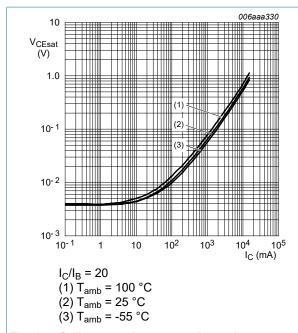


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

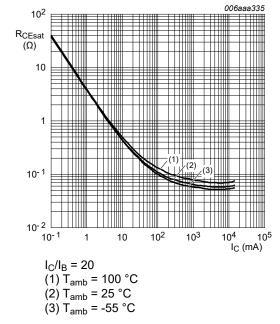


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

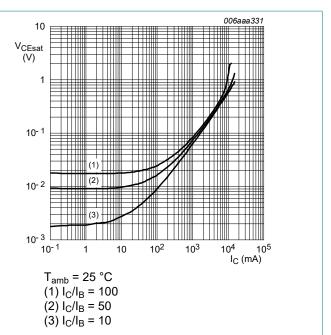


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

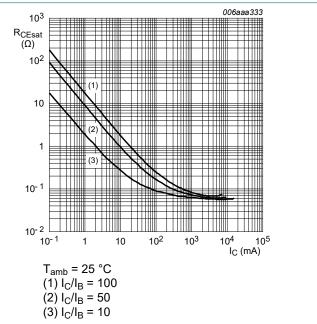


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

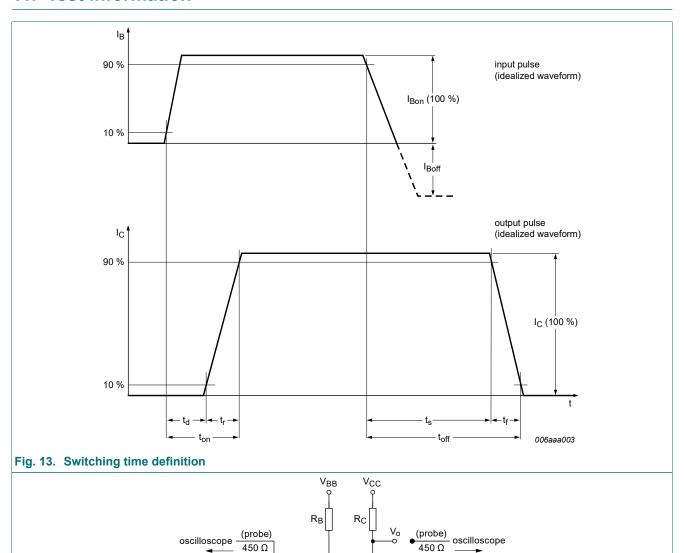


Fig. 14. Test circuit for switching times

 V_{CC} = 12.5 V; I_{C} = 3 A; I_{Bon} = 0.15 A; I_{Boff} = -0.15 A

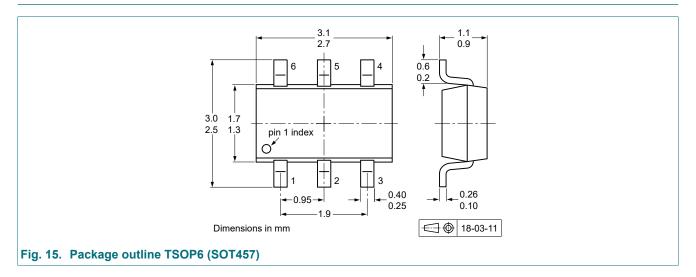
R1

DUT

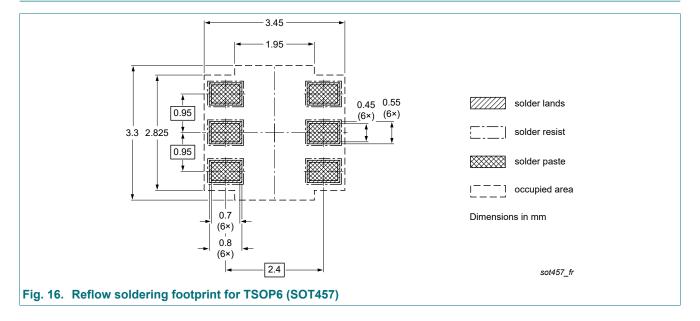
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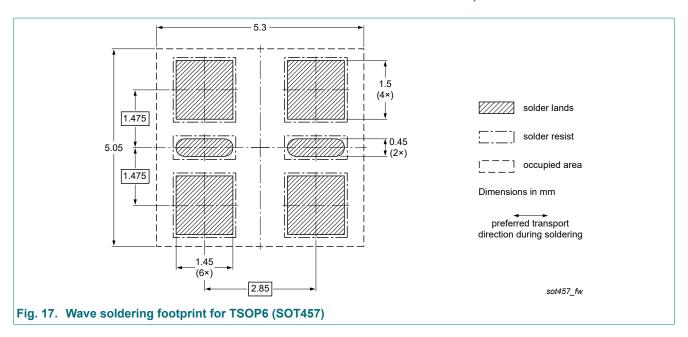
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Table 6. Revision mistory								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PBSS4420D v.3	20250930	Product data sheet	-	PBSS4420D_2				
Modifications:		 Product(s) changed to non-automotive qualification. Please refer to nexperia.com for automotive (-Q) product alternative(s). 						
PBSS4420D_2	20080924	Product data sheet	-	PBSS4420D_1				
PBSS4420D_1	20050421	Product data sheet	-	-				

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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